TOSHIBA Transistor Silicon PNP Epitaxial Type

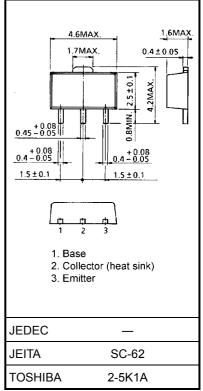
# 2SA2070

### High-Speed Switching Applications DC-DC Converter Applications

- High DC current gain:  $h_{FE} = 200$  to 500 (I<sub>C</sub> = -0.1 A)
- Low collector-emitter saturation voltage:  $V_{CE (sat)} = 0.20 V (max)$
- High-speed switching:  $t_f = 70 \text{ ns}$  (typ.)

#### Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-base voltage		V <sub>CBO</sub>	-50	V	
Collector-emitter voltage		V <sub>CEO</sub>	-50	V	
Emitter-base voltage		V <sub>EBO</sub>	-7	V	
Collector current	DC	Ι <sub>C</sub>	-1.0	А	
	Pulse	I <sub>CP</sub> -2.0			
Base current		Ι <sub>Β</sub>	-0.1	А	
Collector power dissipation	DC	De (Note)	1.0	W	
	t = 10 s	P <sub>C</sub> (Note)	2.0	vv	
Junction temperature		Tj	150	°C	
Storage temperature range		T <sub>stg</sub>	-55 to 150	°C	



Note: Mounted on FR4 board (glass epoxy, 1.6 mm thick, Cu area:  $645 \text{ mm}^2$ )

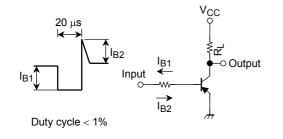
#### Weight: 0.05 g (typ.)

#### Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit	
Collector cut-off current		I <sub>CBO</sub>	$V_{CB} = -50 \text{ V}, \text{ I}_{E} = 0$	_	_	-100	nA	
Emitter cut-off current		I <sub>EBO</sub>	$V_{EB} = -7 V, I_C = 0$	—	_	-100	nA	
Collector-emitter breakdown voltage		V (BR) CEO	I <sub>C</sub> = −10 mA, I <sub>B</sub> = 0	-50	_	_	V	
DC current gain		h <sub>FE</sub> (1)	$V_{CE} = -2 V, I_C = -0.1 A$	200	_	500		
		h <sub>FE</sub> (2)	$V_{CE} = -2 V, I_C = -0.3 A$	125		-		
Collector-emitter saturation voltage		V <sub>CE (sat)</sub>	I <sub>C</sub> = −0.3 A, I <sub>B</sub> = −0.01 mA	_		-0.20	V	
Base-emitter saturation voltage		V <sub>BE (sat)</sub>	I <sub>C</sub> = −0.3 A, I <sub>B</sub> = −0.01 mA	_		-1.10	V	
Collector output capacitance		C <sub>ob</sub>	V <sub>CB</sub> = −10 V, I <sub>E</sub> = 0, f = 1 MHz	_	8	_	pF	
Switching time	Rise time	tr	See Figure 1 circuit diagram.	_	60	_	ns	
	Storage time	t <sub>stg</sub>	V <sub>CC</sub> ≈ –30 V, R <sub>L</sub> = 100 Ω	_	280	_		
	Fall time	t <sub>f</sub>	$I_{B1} = -I_{B2} = -10 \text{ mA}$	—	70	—		

Unit: mm

Marking



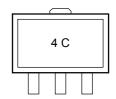
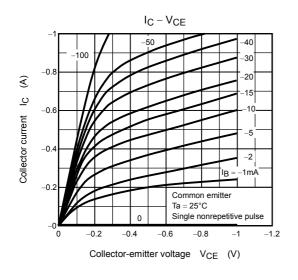
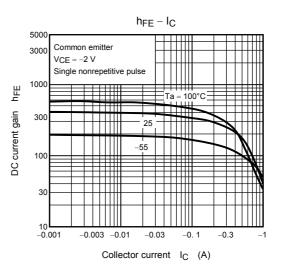
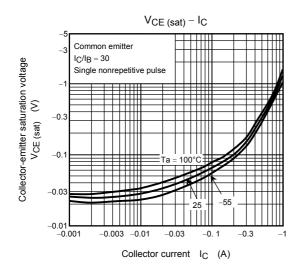


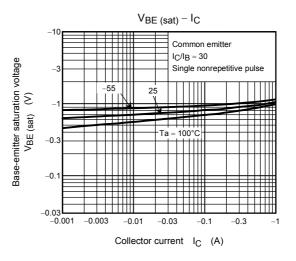
Figure 1 Switching Time Test Circuit & Timing Chart

## **TOSHIBA**

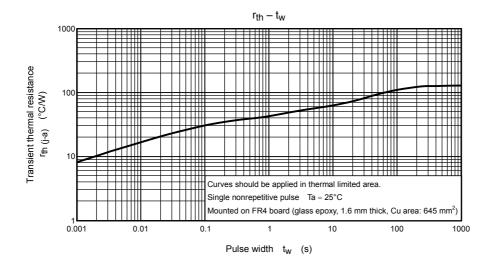








#### $I_{C} - V_{BE}$ Common emitter $V_{CE} = -2 V$ Single nonrepetitive pulse -0.8 E Collector current IC -0.6 -0.4 . 100° 25 -0.2 55 0 0 -0.2 -0.4 -0.6 -0.8 -1.0 -1.2 Base-emitter voltage VBE (V)



Safe Operating Area -10 ms\* 1 ms\* 100 μs\* ₹ IC max (pulsed)\* 10 ms\* 10 μs <u>ں</u> max (continuous 10 Collector current DC operation (Ta =  $25^{\circ}$ C) 100 ms\* -0.3 \*: Single nonrepetitive pulse Ta = 25°C Note that the curves for 100 ms, 10 s and DC operation will be different when the devices aren't mounted on an FR4 board (glass epoxy, 1,6 mm thick, Cu area: 645 mm<sup>2</sup>). These characteristic curves must be derated linearly with increase in temperature. -0.1 CEO max Ħ -0.03 with increase in temperature. -0.01 -0.1 -0.3 -1 -3 -10 -30 -100 Collector-emitter voltage  $V_{CE}$  (V)

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